

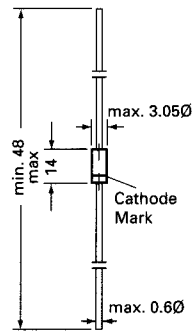
DD300...DD1800

FAST RECOVERY HIGH VOLTAGE SILICON RECTIFIERS

Fast Recovery High Voltage Silicon Rectifiers

Nominal current 20mA
 Repetitive peak reverse voltage 3000 to 18000V

Higher Voltage upon requested



Plastic case

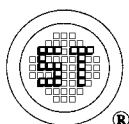
Dimensions in mm

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Type	Reprtitive peak reverse voltage		Nominal current		Cathode Mark	Surge peak reverse voltage
	V_{RRM}	V	I_{FAV}	mA		
DD 300	3000		20		white	4000
DD 600	6000		20		brown	7000
DD 1000	10000		20		blue	12000
DD 1200	12000		20		silver	14000
DD 1400	14000		20		yellow	15500
DD 1600	16000		20		green	19000
DD 1800	18000		20		red	20000

	Symbol	Value	Unit
Nominal current, half wave rectification $T_A = 45^\circ\text{C}$	I_{FAV}	20	mA ¹⁾
Repetitive peak forward current	I_{FRM}	300	mA
Surge current, half cycle 50Hz sine wave, starting from $T_j = 25^\circ\text{C}$	I_{FSM}	5	A
Junction temperature	T_j	150	$^\circ\text{C}$
Operating temperature	T_A	-55 to + 150	$^\circ\text{C}$
Storage temperature	T_s	-55 to + 150	$^\circ\text{C}$

¹⁾ Valid provided if leads are kept at ambient temperature at a distance of 8 mm from case.



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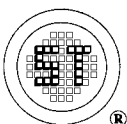
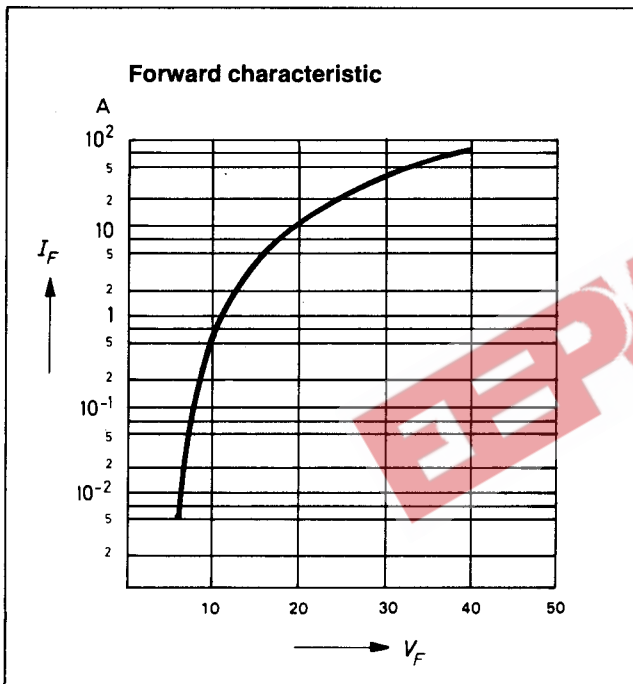


DD300...DD1800

FAST RECOVERY HIGH VOLTAGE SILICON RECTIFIERS

Characteristics

	Symbol	Min.	Typ.	Max.	Unit
Forward Voltage $I_F = 10 \text{ mA}$, $T_J = 25^\circ\text{C}$	V_F	-	-	<40	V
Leakage Current at V_{RRM} $T_J = 25^\circ\text{C}$	I_R	-	-	<1	μA
Reverse Recovery Time from $I_F = 10 \text{ mA}$ to $I_R = 10 \text{ mA}$ to $I_R = 1 \text{ mA}$	t_{rr}	-	-	<55	ns
Thermal Resistance Junction to Ambient Air	T_{thA}	-	-	<60	$\text{K/W}^{(1)}$



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